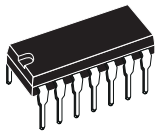
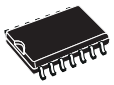
M74HC125

QUAD BUS BUFFER (3-STATE)

- HIGH SPEED:
  t_{PD} = 8ns (TYP.) at V_{CC} = 6V
- LOW POWER DISSIPATION:
  I_{CC} = 4µA(MAX.) at T_A=25°C
- HIGH NOISE IMMUNITY:
  $V_{NIH} = V_{NIL}$ = 28 % V_{CC} (MIN.)
- SYMMETRICAL OUTPUT IMPEDANCE:
  $|I_{OH}| = I_{OL}$ = 6mA (MIN)
- BALANCED PROPAGATION DELAYS:
  $t_{PLH} \cong t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE:
  V_{CC} (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 125



DIP



SOP

TSSOP

ORDER CODES

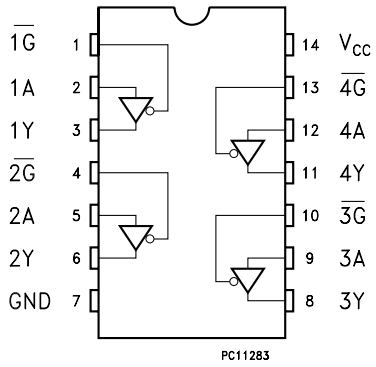
PACKAGE	TUBE	T & R
DIP	M74HC125B1R	
SOP	M74HC125M1R	M74HC125RM13TR
TSSOP		M74HC125TTR

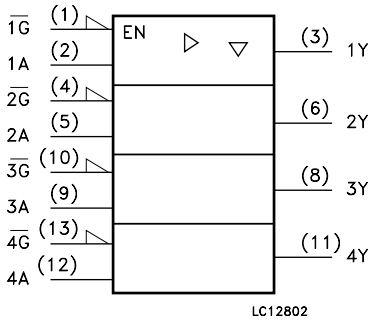
DESCRIPTION

The M74HC125 is an high speed CMOS QUAD BUFFER (3-STATE) fabricated with silicon gate C^2MOS technology.
The device requires the 3-STATE control input $\overline{G}$ to be set high to place the output into the high impedance state.

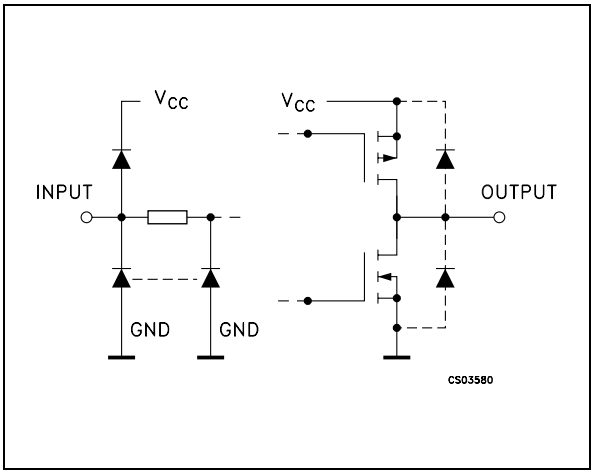
All inputs are equipped with protection circuits against static discharge and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS





INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 4, 10, 13	$\overline{1G}$ TO $\overline{4G}$	Output Enable Input
2, 5, 9, 12	1A TO 4A	Data Inputs
3, 6, 8, 11	1Y TO 4Y	Data Outputs
7	GND	Ground (0V)
14	V_{CC}	Positive Supply Voltage

TRUTH TABLE

A	$\overline{G}$	Y
X	H	Z
L	L	L
H	L	H

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7	V
V_I	DC Input Voltage	-0.5 to V_{CC} + 0.5	V
V_O	DC Output Voltage	-0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Current	± 35	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 70	mA
P_D	Power Dissipation	500(*)	mW
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied
(*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Value	Unit
V_{CC}	Supply Voltage		2 to 6	V
V_I	Input Voltage		0 to V_{CC}	V
V_O	Output Voltage		0 to V_{CC}	V
T_{op}	Operating Temperature		-55 to 125	°C
t_r, t_f	Input Rise and Fall Time	V_{CC} = 2.0V	0 to 1000	ns
		V_{CC} = 4.5V	0 to 500	ns
		V_{CC} = 6.0V	0 to 400	ns

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value							Unit
		V_{CC} (V)		T_A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	2.0		1.5			1.5		1.5		V
		4.5		3.15			3.15		3.15		
		6.0		4.2			4.2		4.2		
V_{IL}	Low Level Input Voltage	2.0				0.5		0.5		0.5	V
		4.5				1.35		1.35		1.35	
		6.0				1.8		1.8		1.8	
V_{OH}	High Level Output Voltage	2.0	I_O=-20 µA	1.9	2.0		1.9		1.9		V
		4.5	I_O=-20 µA	4.4	4.5		4.4		4.4		
		6.0	I_O=-20 µA	5.9	6.0		5.9		5.9		
		4.5	I_O=-6.0 mA	4.18	4.31		4.13		4.10		
		6.0	I_O=-7.8 mA	5.68	5.8		5.63		5.60		
V_{OL}	Low Level Output Voltage	2.0	I_O=20 µA		0.0	0.1		0.1		0.1	V
		4.5	I_O=20 µA		0.0	0.1		0.1		0.1	
		6.0	I_O=20 µA		0.0	0.1		0.1		0.1	
		4.5	I_O=6.0 mA		0.17	0.26		0.33		0.40	
		6.0	I_O=7.8 mA		0.18	0.26		0.33		0.40	
I_I	Input Leakage Current	6.0	V_I = V_{CC} or GND			± 0.1		± 1		± 1	µA
I_{OZ}	High Impedance Output Leakage Current	6.0	V_I = V_{IH} or V_{IL} V_O = V_{CC} or GND			± 0.5		± 5		± 10	µA
I_{CC}	Quiescent Supply Current	6.0	V_I = V_{CC} or GND			4		40		80	µA

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 6ns$)

Symbol	Parameter	Test Condition			Value							Unit
		V_{CC} (V)	C_L (pF)		T_A = 25°C			-40 to 85°C		-55 to 125°C		
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t_{TLH} t_{THL}	Output Transition Time	2.0	50			20	60		75		90	ns
		4.5				6	12		15		18	
		6.0				5	10		13		15	
t_{PLH} t_{PHL}	Propagation Delay Time	2.0	50			36	75		95		110	ns
		4.5				9	15		19		22	
		6.0				8	13		16		19	
		2.0	150			52	105		130		160	ns
		4.5				13	21		26		32	
		6.0				11	18		22		27	
t_{PZL} t_{PZH}	High Impedance Output Enable Time	2.0	50	R_L = 1 KΩ		36	75		95		110	ns
		4.5				9	15		19		22	
		6.0				8	13		16		19	
		2.0	150	R_L = 1 KΩ		52	105		130		160	ns
		4.5				13	21		26		32	
		6.0				11	18		22		27	
t_{PLZ} t_{PHZ}	High Impedance Output Disable Time	2.0	50	R_L = 1 KΩ		48	80		100		120	ns
		4.5				12	16		20		24	
		6.0				10	14		17		20	

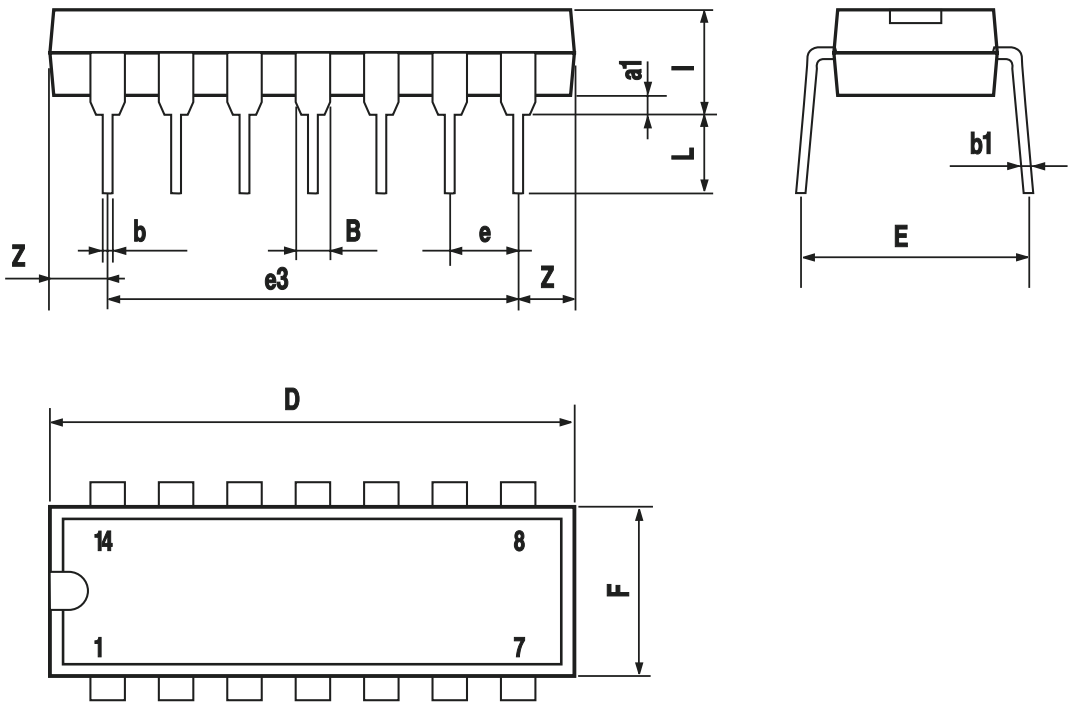
CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition		Value							Unit
		V_{CC} (V)		T_A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
C_{IN}	Input Capacitance	5.0			5	10		10		10	pF
C_{PD}	Power Dissipation Capacitance (note 1)	5.0			35						pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/4$ (per buffer)

Plastic DIP-14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



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